NSN 5962-01-241-8082

Memory Microcircuit - Page 1 of 2



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Body Len	ath-
1.285 inch	-
Body Wid	
0.310 inch	
Body Heig	
0.175 inch	
	Power Dissipation Rating:
413.0 milli	
	Tempurature Range:
	i.0 degrees celsius
	empurature Range:
	0.0 degrees celsius
End Appl	-
	sembl 84-27401-001
Features	
Hermetica	ly sealed and burn in and electrostatic sensitive and programmable and high performance
Inclosure	
Ceramic	
	Configuration:
Dual-in-lin	
Output Lo	gic Form:
	- entary-metal oxide-semiconductor logic
	uit Pattern:
14 input	
Criticality	Code Justification:
Feat	
Case Out	ine Source And Designator:
D-9 mil-m·	38510
Terminal	Surface Treatment:
Solder	
Voltage R	ating And Type Per Characteristic:
-5.0 volts	power source and 7.0 volts power source
Time Rati	ng Per Chacteristic:
50.00 nan	oseconds propagation delay time, low to high level output and 50.00 nanoseconds propagation delay time, high to low level
output	
Memory [Device Type:
Rom	
Special F	eatures:
Nuclear h	ardness critical item
Test Data	Document:
96906-mil	std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

NSN 5962-01-241-8082

Memory Microcircuit - Page 2 of 2

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

A458a0

